

# LPR30

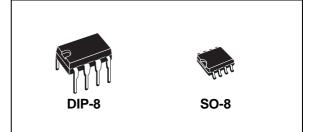
## LOW DROP VOLTAGE REGULATOR DRIVE FOR EXTERNAL N-CHANNEL POWER MOSFET

- VERY LOW DROPOUT POWER MOSFET DRIVER
- HIGH PRECISION Vref =  $2.5V (\pm 2\%)$
- VERY LOW CURRENT DRAIN (TYP. 2mA)
- REFERENCE OUTPUT CURRENT UP TO 20mA
- OPERATING SUPPLY VOLTAGE FROM 5V TO 30V
- MAXIMUM INPUT VOLTAGE ON-GATE PIN (N. 8) UP TO 60V
- INTERNAL CURRENT LIMIT OPERATIONAL AMPLIFIER OFFSET TRIMMED AT 50mV ± 10mV
- NO CAPACITOR IS NEEDED FOR STABILITY OF REFERENCE OUTPUT
- TEMPERATURE RANGE 0 °C TO 70 °C

#### APPLICATION

- ULTRA HIGH CURRENT ULTRA LOW DROPOUT VOLTAGE REGULATOR
- CONSTANT HIGH CURRENT SOURCE

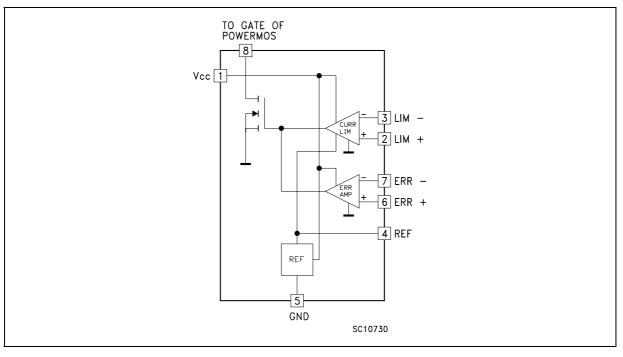
#### **BLOCK DIAGRAM**



- LOW PARTS COUNT 5V TO 3.3V
- COMPUTER SUPPLY LOW NOISE/LOW DROP SMPS POST
- LOW NOISE/LOW DROP SMPS POST REGULATOR

#### DESCRIPTION

The LPR30 is a very Low Dropout Regulator Controller in a single IC solution for very high current low dropout linear voltgage regulator. It uses an external N-CHANNEL POWER MOSFET as the linear pass element. The LPR30 features a dropout voltage as low as the R<sub>DS(on)</sub> of the



external Power MOSFET multiplied by the output current. Consequently the output current can be as high as the POWER MOSFET can provide (also using an adeguate heatsink).

The V<sub>CC</sub> of the LPR30 range from 5V to 30V. For very low drop voltage operation, the LPR30 requires an external gate drive supply to provide the control voltage needed to drive the gate of the external POWER MOSFET.

The regulator output is constant-current limited when the controller detects 50mV across an external sense resistor.

It has an internal high precision (± 2%) Voltage Reference at 2.5V

The output regulated voltage is possible to program to any voltage from 1V to more than 50V.

Flexible design is achieved by the availability of the Voltage Reference Output through an external pin (N.4) that is able to supply more than 20mA as load current. The LPR30 is available in 8 pin plastic DIP and in SO-8 for SMD. In both package versions it is able to operate from  $0^{\circ}$ C to  $70^{\circ}$ C.

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#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	DC Input Voltage	36	V
I <sub>oref</sub>	Reference Output Current	Internally Limited	
P <sub>tot</sub>	Power Dissipation	1	W
T <sub>op</sub>	Operating Junction Temperature Range	0 to 70	°C
$T_{stg}$	Storage Temperature Range	- 40 to 150	°C
V <sub>gate</sub>	Maximum Gate Voltage (pin n8)	60	V
I <sub>gate</sub>	Maximum Gate Current (pin n8)	200	mA

Absolute Maximum Ratings are those values beyond which damage to the device may occur.

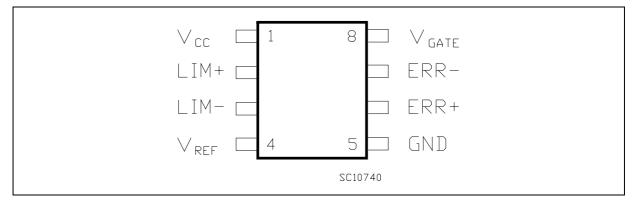
Functional operation under these conditions is not implied.

#### THERMAL DATA

Symbol	Parameter		DIP-8	SO-8	Unit
$R_{thj-amb}$	Thermal Resistance Junction-ambient (*)	Max	130 to 180	100 to 150	°C/W

(\*) This value depends from thermal design of PCB on which the device is mounted.

#### **CONNECTION DIAGRAM** (top view)



#### **ORDERING NUMBERS**

Туре	DIP-8	SO-8	SO-8 (tape & reel)
LPR30	LPR30N	LPR30D	LPR30D-TR

**ELECTRICAL CHARACTERISTICS** (Refer to the test circuits,  $V_{CC}$  = 10V,  $T_j$  = 25 °C unless otherwise specified.

#### GENERAL

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vcc	Operating Supply Voltage		5		30	V
Icc	Supply Current			2	4	mA
V <sub>osat</sub>	Output Saturation Voltage			280	500	mV
Ι <sub>ΟLΚ</sub>	Output Leakage Current	$V_{CC} = 5 V$ $V_{O} = 60 V$ ERR(-), LIM(-) = 0V ERR(+), LIM(+) = 1V			100	μA

#### **REFERENCE BLOCK**

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
VREF	Reference Output Voltage		2.45	2.5	2.55	V
Ι <sub>κ</sub>	Reference Output Current		20			mA
$\Delta V_{REF} / \Delta I_{K}$	Reference Output Voltage Change	$I_{K} = 1$ to 20 mA $C_{REF} = 0 \text{ pF}$		3		mV
SVR	Supply Voltage Rejection	$V_{IN} < 10 \text{ V} \pm 1 \text{V} \text{ f} = 120 \text{ Hz}  C_{REF} = 0 \text{ pF}$		70		dB
eN	Output Noise	B = 10  Hz to  10  KHz I <sub>K</sub> = 10 mA C <sub>REF</sub> = 0 pF		50		μV

#### ERROR AMPLIFIER BLOCK

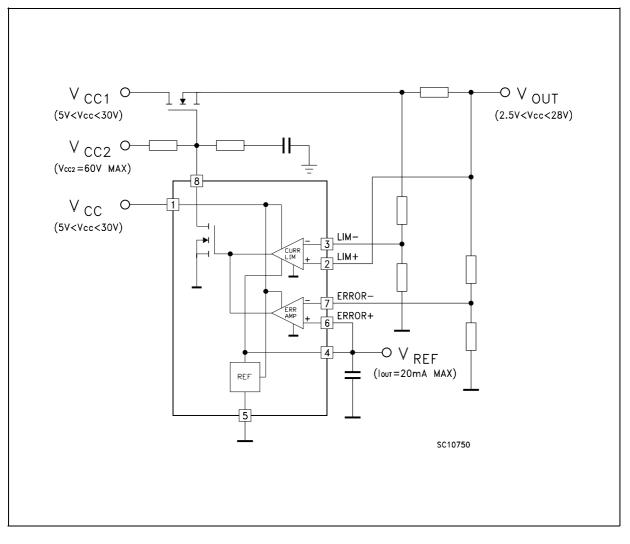
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Ι <sub>Β</sub>	Input Bias Current			0.3	1	μΑ
Vos	Input Offset Voltage	$V_{CC} = 5 \text{ to } 30 \text{ V}$ $T_j = 0 \text{ to } 70 ^{\circ}\text{C}$			5	mV
los	Input Offset Current			5	50	nA
Gv	Open Loop Gain	$T_{j} = 0 \text{ to } 70 \ ^{\circ}\text{C}$	80			dB
V <sub>СМ</sub>	Input Common Mode Voltage Range	$T_j = 0 \text{ to } 70 \ ^{\circ}\text{C}$	1		V <sub>cc</sub> -1	V
CMR	Common Mode Rejection			70		dB
SVR	Supply Voltage Rejection		70 60			dB dB

#### CURRENT LIMITING BLOCK

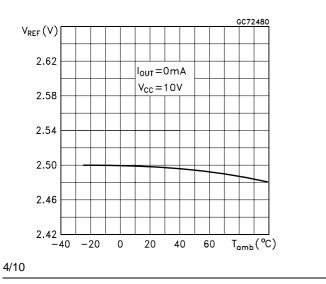
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Ι <sub>Β</sub>	Input Bias Current				0.5	μA
Vos	Input Offset Voltage	$T_{j} = 0 \text{ to } 70 \ ^{\circ}\text{C}$	40		60	V
Gv	Open Loop Gain	$T_j = 0$ to 70 °C	50			dB
V <sub>CM</sub>	Input Common Mode Voltage Range	$T_{j} = 0 \text{ to } 70 ^{\circ}\text{C}$	0		V <sub>CC</sub> -3	V

### LPR30

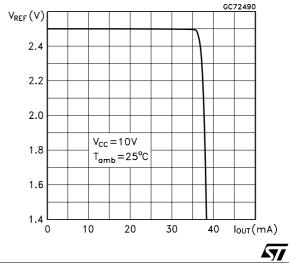
#### **TEST CIRCUIT**



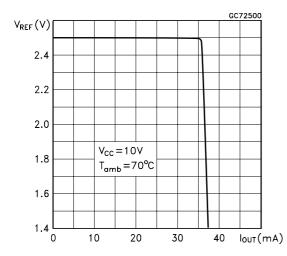
#### TYPICAL PERFORMANCE CHARACTERISTICS Reference Output Voltage vs Temperature



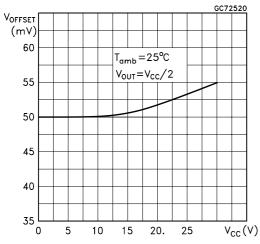
#### Reference Output Voltage vs Load Current



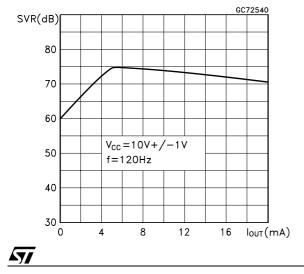


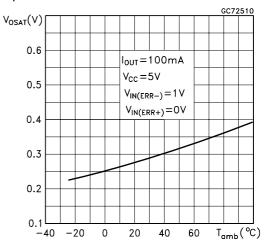


# Current Limit Input Offset Voltage vs Supply Voltage



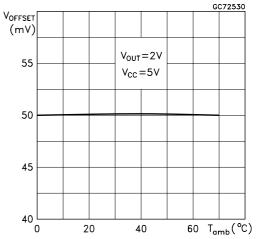
Reference Supply Voltage Rejection vs Output Current



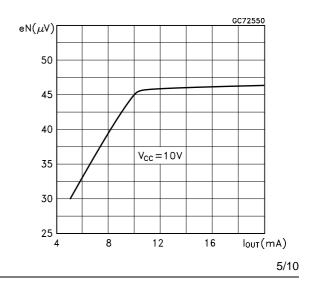


#### Error Amplifier Output Saturation Voltage vs Temperature



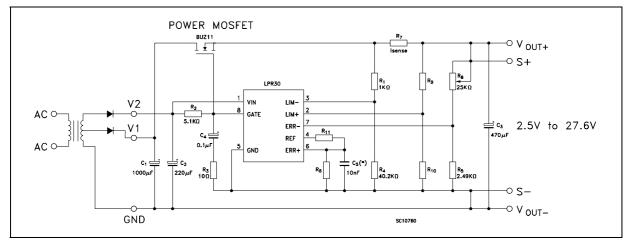


Reference Output Noise vs Output Current

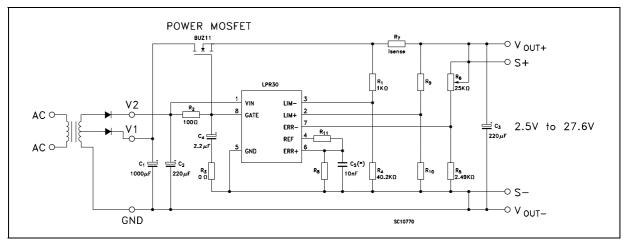


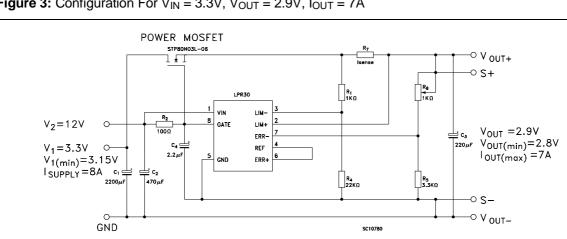
### **APPLICATION INFORMATION**

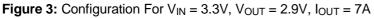
#### Figure 1: LPR30 Typical Application







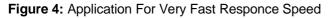


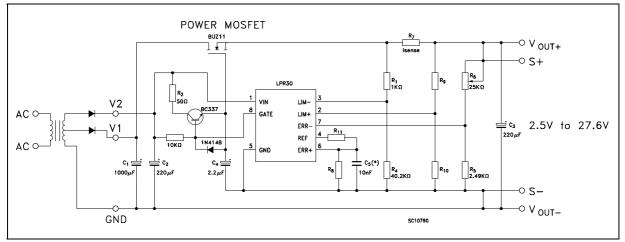


(\*) This capacitor improves noise performance; can be omitted in most applications

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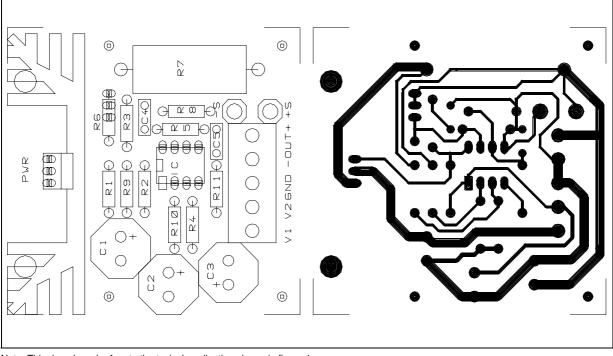
### **APPLICATION INFORMATION** (contiued)





(\*) This capacitor improves noise performance; can be omitted in most applications

#### STANDARD APPLICATION DEMOBOARD

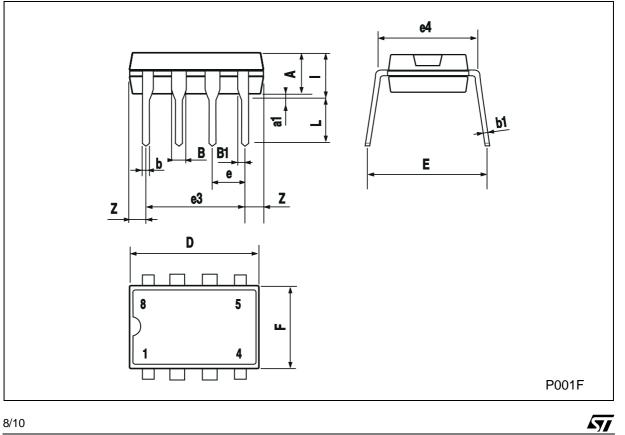


Note: This demoboard refers to the typical application shown in figure 1



DIM.		mm	•		inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А		3.3			0.130	
a1	0.7			0.028		
В	1.39		1.65	0.055		0.065
B1	0.91		1.04	0.036		0.041
b		0.5			0.020	
b1	0.38		0.5	0.015		0.020
D			9.8			0.386
E		8.8			0.346	
е		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			7.1			0.280
I			4.8			0.189
L		3.3			0.130	

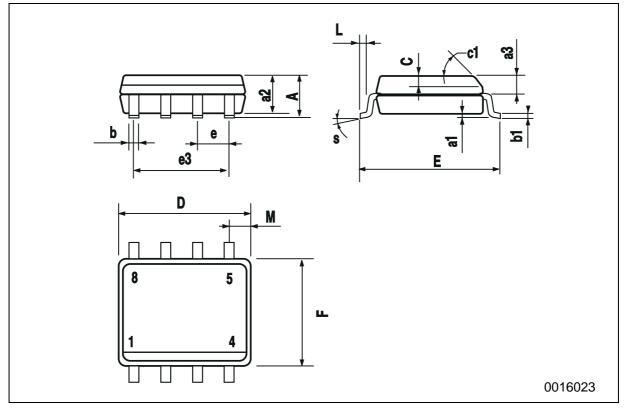




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DIM.		mm			inch		
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			1.75			0.068	
a1	0.1		0.25	0.003		0.009	
a2			1.65			0.064	
a3	0.65		0.85	0.025		0.033	
b	0.35		0.48	0.013		0.018	
b1	0.19		0.25	0.007		0.010	
С	0.25		0.5	0.010		0.019	
c1			45	(typ.)			
D	4.8		5.0	0.188		0.196	
E	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		3.81			0.150		
F	3.8		4.0	0.14		0.157	
L	0.4		1.27	0.015		0.050	
М			0.6			0.023	
S			8 (r	max.)			





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